TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

# 2SA1160

# Strobe Flash Applications Medium Power Amplifier Applications

• High DC current gain and excellent hFE linearity

:  $h_{FE}$  (1) = 140 to 600 ( $V_{CE}$  = -1 V,  $I_{C}$  = -0.5 A)

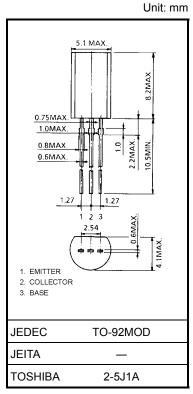
 $h_{FE}(2) = 60 \text{ (min)}, 120 \text{ (typ.)} \text{ (V}_{CE} = -1 \text{ V}, I_{C} = -4 \text{ A)}$ 

• Low saturation voltage

 $: V_{CE (sat)} = -0.5 \text{ V (max) (I}_{C} = -2 \text{ A}, I_{B} = -50 \text{ mA)}$ 

#### **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	-20	V	
Collector-emitter voltage		V <sub>CEO</sub>	-10	V	
Emitter-base voltage		V <sub>EBO</sub>	-6	V	
Collector current	DC	IC	-2	А	
	Pulsed (Note 1)	ICP	-4		
Base current		ΙΒ	-2	Α	
Collector power dissipation		PC	900	mW	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



Weight: 0.36 g (typ.)

Note 1: Pulse width = 10 ms (max), duty cycle = 30% (max)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

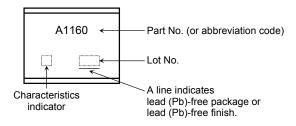
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

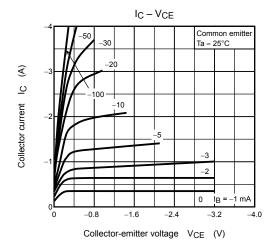
## Electrical Characteristics (Ta = 25°C)

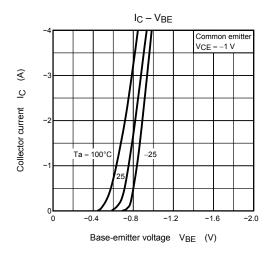
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = -20 \text{ V}, I_E = 0$	_	_	-100	nA
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = -6 \text{ V}, I_C = 0$	_	_	-100	nA
Collector-emitter breakdown voltage	V (BR) CEO	$I_C = -10 \text{ mA}, I_B = 0$	-10	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	$I_E = -1 \text{ mA}, I_C = 0$	-6	_	_	V
DC current gain	h <sub>FE (1)</sub> (Note 3)	$V_{CE} = -1 \text{ V, } I_{C} = -0.5 \text{ A}$	140	_	600	
Collector-emitter saturation voltage	h <sub>FE (2)</sub>	$V_{CE} = -1 \text{ V, } I_{C} = -4 \text{ A}$	60	120	_	
Base-emitter saturation voltage	V <sub>CE</sub> (sat)	$I_C = -2 \text{ A}, I_B = -50 \text{ mA}$	_	-0.20	-0.50	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -1 \text{ V, } I_{C} = -2 \text{ A}$	_	-0.83	-1.5	V
Transition frequency	f <sub>T</sub>	$V_{CE} = -1 \text{ V, } I_{C} = -0.5 \text{ A}$	_	140	_	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	_	50	_	pF

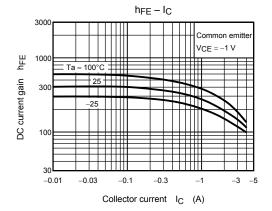
Note 3:  $h_{FE\ (1)}$  Classification A: 140 to 280, B: 200 to 400, C: 300 to 600

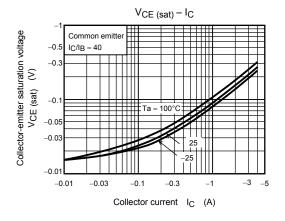
### Marking

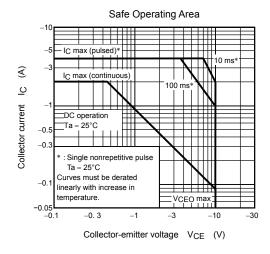


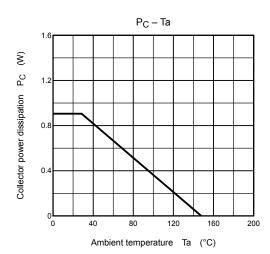












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